PHYC 569, Advanced Topics in Modern Optics

(Laser Physics II: PHYC/ECE 564)

Fall 2016

Homework #3, Due Tue Oct. 4

Instructor: M. Sheik-Bahae

1.

(a) Find the e-h carrier density (n_t) required to just invert GaAs having E_g=1.43, m_e=0.07m_0 and m_h=0.5m_0. Assume T=300K.

(b) For a gain layer of d=1μm, calculate the steady-state current density (J_t) needed to sustain the above carrier density if the radiative recombination rate (given by BN_eN_h) is the dominating recombination mechanism where B≅ 2×10^{-10} cm^3/sec.

(c) Find the peak value of the gain γ, its peak wavelength λ_{peak}, and the width of the gain Δλ, if the current density is increased to 2×J_t.

(d) Repeat (a) and (b) for T=77 K to appreciate the temperature dependence of the threshold current of semiconductor lasers.

2.

(a) Derive an expression for the radiative recombination rate $B=R/N_{eh}^2$ at low injection carrier density limit. Identify the temperature dependence. Estimate B for GaAs.

(b) Derive an expression for the mean fluorescence wavelength (λ_f) and plot λ_f/λ_g as a function of temperature for GaAs (Use low carrier injection approximation).

Use van Roosbroeck-Shockley (reciprocity) relation: $R(\nu)=\dfrac{8\pi n^2\nu^2}{c^2}\alpha_0(h\nu)\{f_c(1-f_v)\}$

$$R = BN^2 = \int R(\nu)d\nu$$

3. Consider a symmetric optical slab waveguide shown below.

(a) For λ_0=1.5 μm (in free space), find the number of TE modes in this waveguide.

(b) What are the confinement factors (Γ) for TE_0 and TE_1 modes?